

applied surface science

A journal devoted to the properties of interfaces
in relation to the synthesis and behaviour of materials

Editors:

L.C. Feldman, Murray Hill, NJ, USA

W.F. van der Weg, Utrecht, The Netherlands

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W.F. van der Weg, Utrecht, The Netherlands

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| | Electrical properties |
| Band structure | Electron bombardment |
| Benzene | Electron diffraction |
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| Borides | Electron energy loss spectroscopy |
| Boron | Electron microscopy |
| | Electron scattering |
| Cadmium | Electron spin resonance |
| Cadmium selenide | Electron stimulated desorption |
| Cadmium sulphide | Ellipsometry |
| Cadmium telluride | Epitaxy |
| Calcium | Etching |
| Carbides | Ethylene |
| Carbon | Evaporation |
| Carbon dioxide | |
| Carbon monoxide | Field ion microscopy |
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| Cathodes | |
| Ceramics | Gallium antimonide |
| Chalcogenides | Gallium arsenide |
| Chemical vapour deposition | Gallium phosphide |
| Chemisorption theory | Germanium |
| Chromium | Glass |
| Clusters | Gold |
| Coatings | Grain boundaries |
| Cobalt | Graphite |

- Halides
Hall effect
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Halogenides
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Photoelectron spectroscopy
Photon emission
Piezoelectric effect
Plasma processing
Platinum
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- Radiation damage
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Raman spectroscopy
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Rhodium
Ruthenium
- Schottky barrier
Secondary ion mass spectroscopy
Second harmonic generation
Selenium
Semiconductors
Semiconductor-semiconductor interfaces
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Silicides
Silicon
Silicon carbide
Silicon nitride
Silicon oxide
Silver

- | | |
|--|--------------------------|
| Solar cells | Thin films |
| Solid phase epitaxy | Tin |
| Sputter deposition | Tin oxide |
| Sputtering | Titanium |
| Steel | Titanium dioxide |
| Sulphides | Titanium oxide |
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| Surface structure | X-ray emission |
| Surface thermodynamics | X-ray scattering |
| | |
| Tantalum | Yttrium |
| Tellurium | |
| Thallium | Zinc |
| Thermal desorption | Zinc oxide |
| | Zirconium |

Introduction to Zeolite Science and Practice

edited by H. van Bekkum, *TU Delft, Delft, The Netherlands*, E.M. Flanigen, *UOP, Tarrytown, NY, USA* and J.C. Jansen, *TU Delft, Delft, The Netherlands*

(Studies in Surface Science and Catalysis, 58)

Zeolites and related molecular sieves have quickly become important pathways to new opportunities in the fields of oil processing and petrochemical synthesis. The signs of intense activity in both industry and academia are evident: burgeoning papers and patent applications; increasing numbers of industrial zeolite-based processes and their rapid expansion into organic chemicals manufacturing; recent progress in zeolite accessibility range, matrix behaviour, lattice components and satellite structures; and the recognition that zeolites, which are stable and can be regenerated, may be incorporated into new, environmentally friendly processes.

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